



PMZB290UNE

20 V, single N-channel Trench MOSFET

Rev. 3 — 23 March 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- Ultra thin package profile of 0.37mm

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

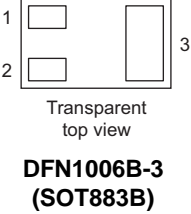
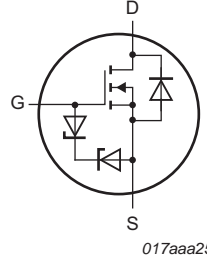
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	20	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	1	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 500\text{ mA}; T_j = 25\text{ °C}$	-	290	380	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PMZB290UNE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

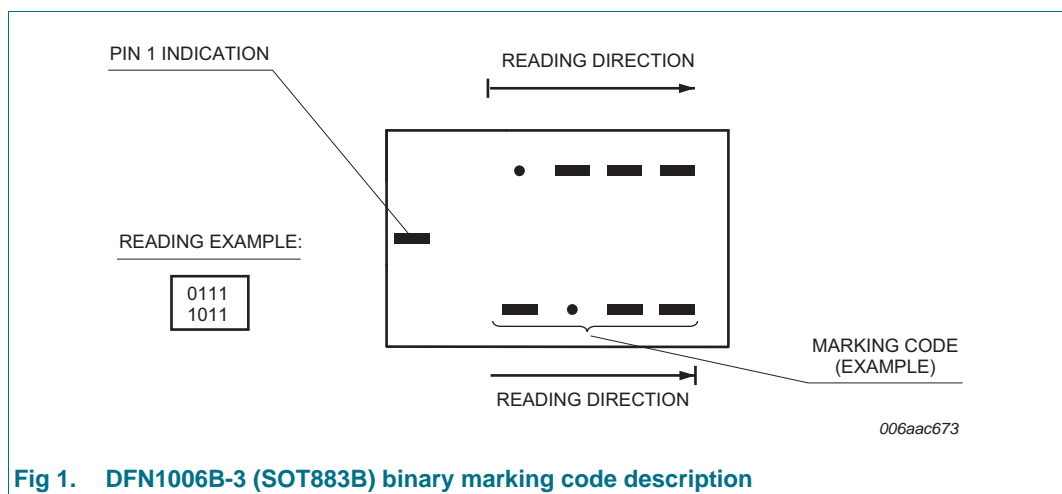
4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB290UNE	0000 0110

[1] For DFN1006B-3 (SOT883B) binary marking code description see [Figure 1](#).

4.1 Binary marking code description



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C	-	20	V	
V _{GS}	gate-source voltage		-8	8	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	1	A
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	625	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs	-	4	A	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature		-55	150	°C	
T _{amb}	ambient temperature		-55	150	°C	
T _{stg}	storage temperature		-65	150	°C	

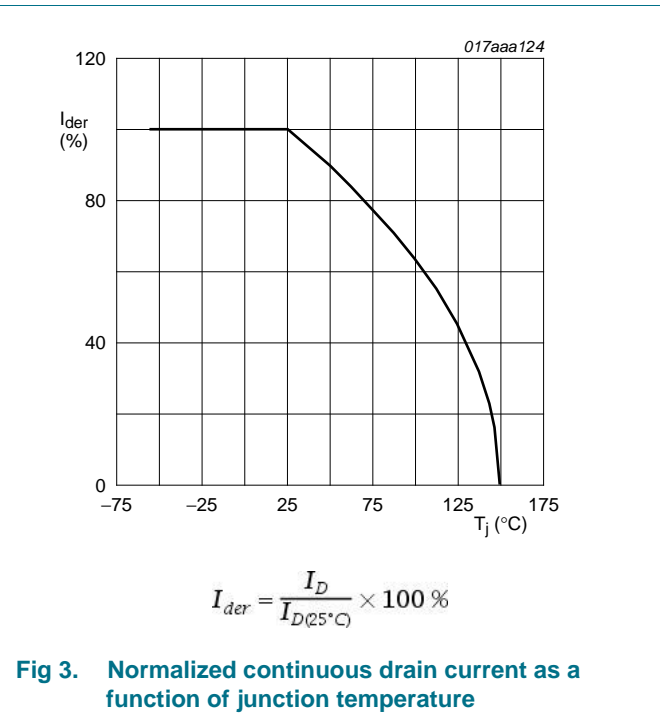
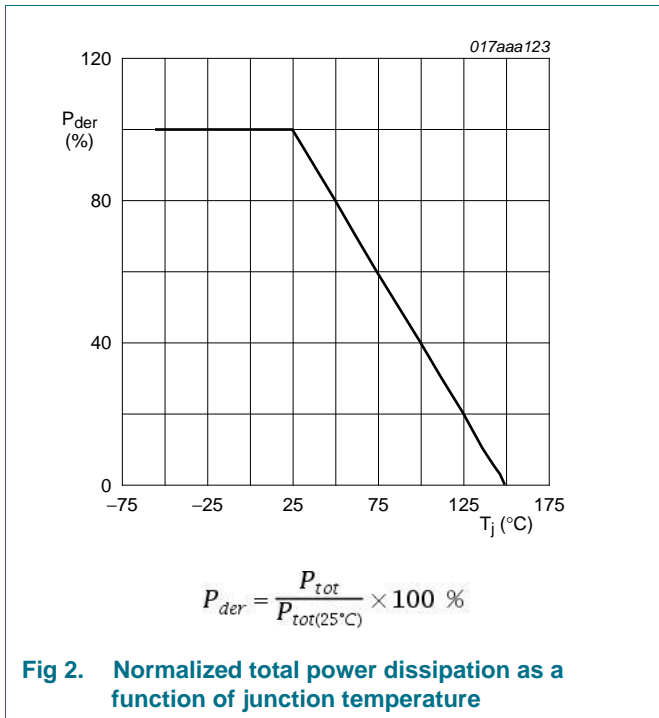
Source-drain diode

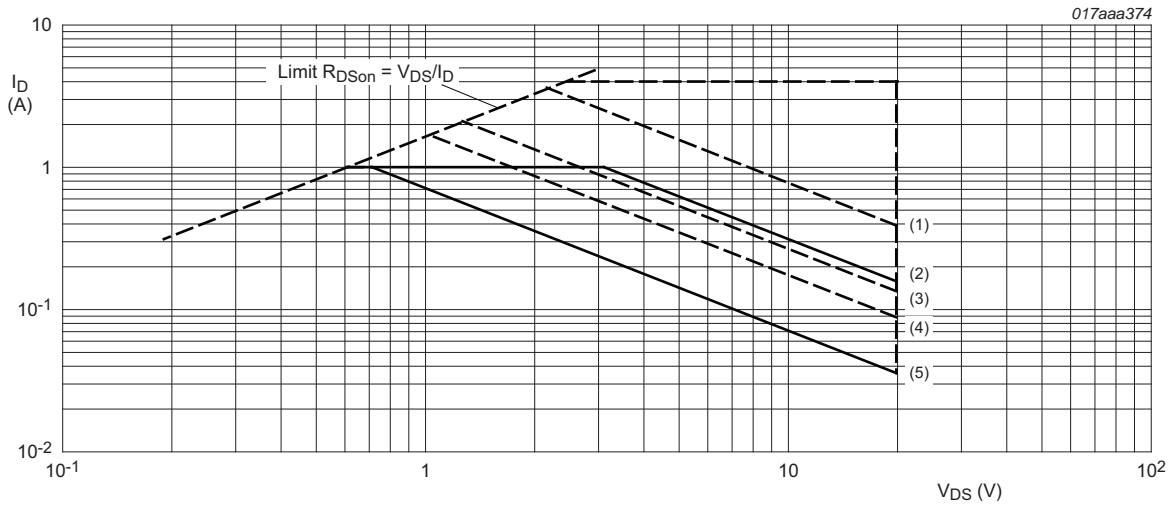
I _S	source current	T _{amb} = 25 °C	[1]	-	680	mA
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ESD maximum rating

V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V
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- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.





I_{DM} = single pulse

(1) $t_p = 1$ ms

(2) DC; $T_{sp} = 25$ °C

(3) $t_p = 10$ ms

(4) $t_p = 100$ ms

(5) DC; $T_{amb} = 25$ °C; drain mounting pad 1 cm²

Fig 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	40	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

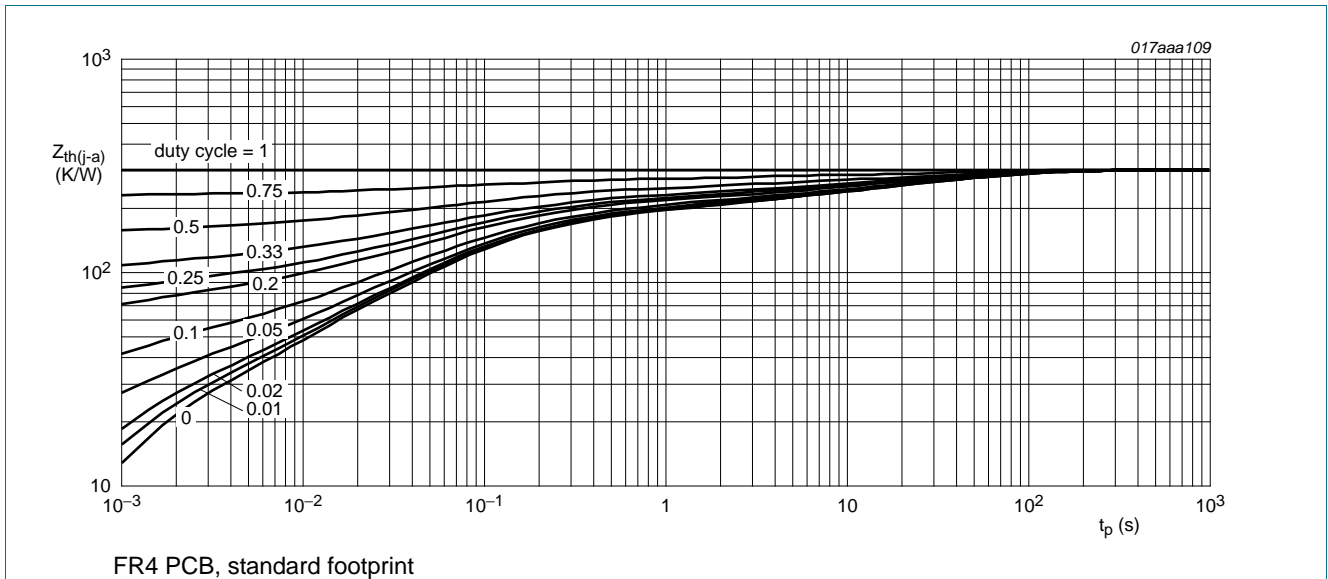


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

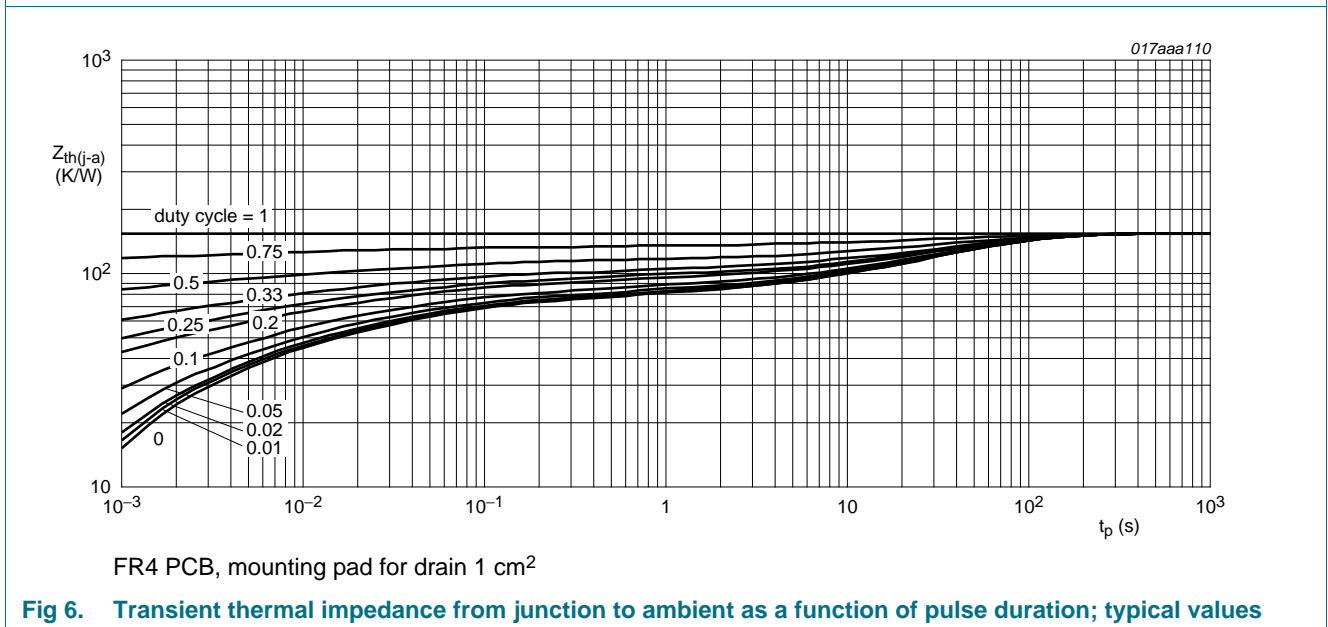
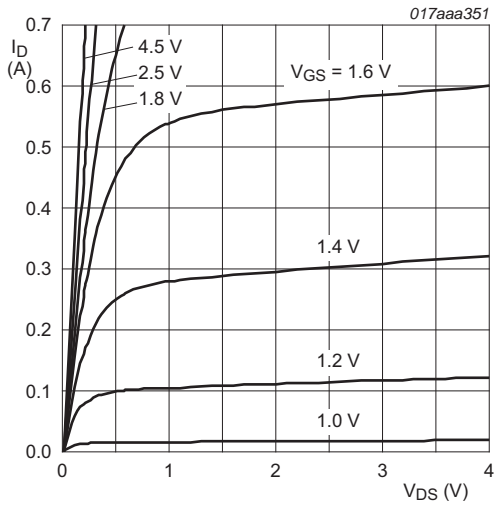


Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

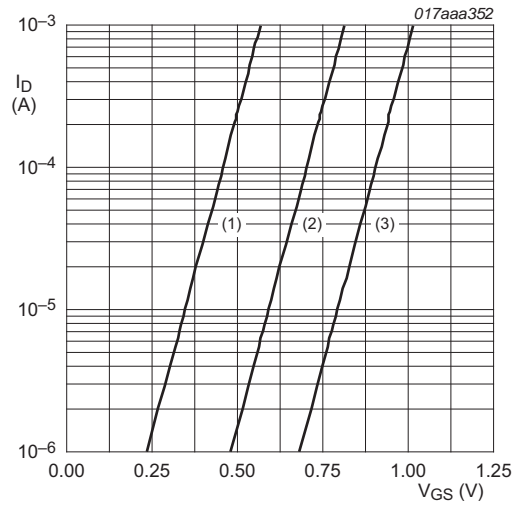
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$	0.5	0.75	0.95	V
I_{DSS}	drain leakage current	$V_{DS} = 20 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 20 V$; $V_{GS} = 0 V$; $T_j = 150 \text{ }^\circ C$	-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	2	μA
		$V_{GS} = -8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	2	μA
		$V_{GS} = 4.5 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	500	nA
		$V_{GS} = -4.5 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	500	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 V$; $I_D = 500 \text{ mA}$; $T_j = 25 \text{ }^\circ C$	-	290	380	m Ω
		$V_{GS} = 4.5 V$; $I_D = 500 \text{ mA}$; $T_j = 150 \text{ }^\circ C$	-	460	610	m Ω
		$V_{GS} = 2.5 V$; $I_D = 400 \text{ mA}$; $T_j = 25 \text{ }^\circ C$	-	420	620	m Ω
		$V_{GS} = 1.8 V$; $I_D = 100 \text{ mA}$; $T_j = 25 \text{ }^\circ C$	-	600	1100	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10 V$; $I_D = 200 \text{ mA}$; $T_j = 25 \text{ }^\circ C$	-	1.6	-	S
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 V$; $I_D = 500 \text{ mA}$; $V_{GS} = 4.5 V$; $T_j = 25 \text{ }^\circ C$	-	0.45	0.68	nC
Q_{GS}	gate-source charge		-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.15	-	nC
C_{iss}	input capacitance	$V_{DS} = 10 V$; $f = 1 \text{ MHz}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	55	83	pF
C_{oss}	output capacitance		-	15	-	pF
C_{rss}	reverse transfer capacitance		-	7	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10 V$; $R_L = 250 \Omega$; $V_{GS} = 4.5 V$; $R_{G(ext)} = 6 \Omega$; $T_j = 25 \text{ }^\circ C$	-	6	12	ns
t_r	rise time		-	4	-	ns
$t_{d(off)}$	turn-off delay time		-	86	172	ns
t_f	fall time		-	31	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 300 \text{ mA}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	0.48	0.77	1.2	V



$T_j = 25\text{ }^\circ\text{C}$

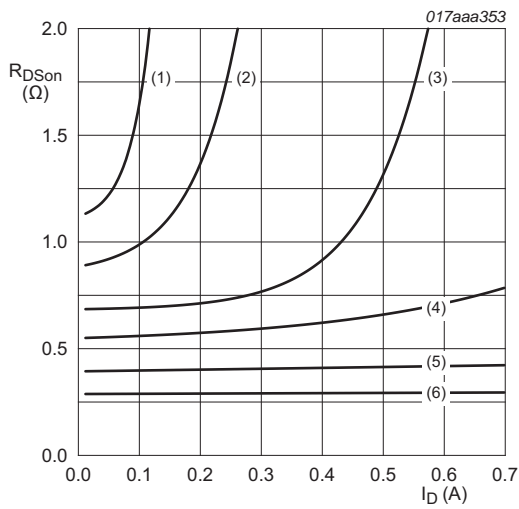
Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

- (1) minimum values
- (2) typical values
- (3) maximum values

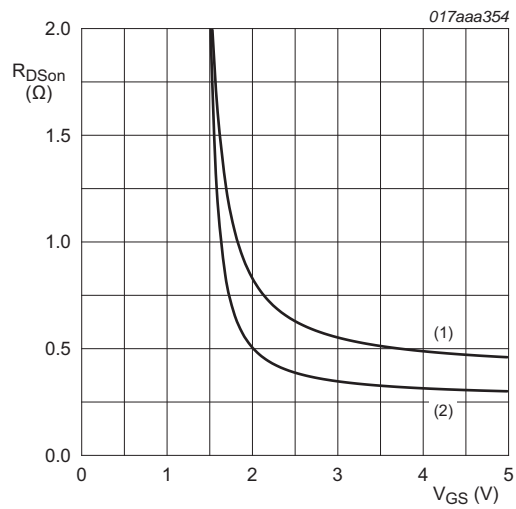
Fig 8. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25\text{ }^\circ\text{C}$

- (1) $V_{GS} = 1.3\text{ V}$
- (2) $V_{GS} = 1.4\text{ V}$
- (3) $V_{GS} = 1.6\text{ V}$
- (4) $V_{GS} = 1.8\text{ V}$
- (5) $V_{GS} = 2.5\text{ V}$
- (6) $V_{GS} = 4.5\text{ V}$

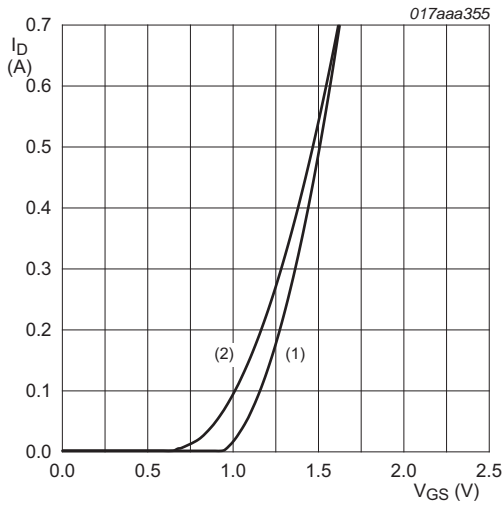
Fig 9. Drain-source on-state resistance as a function of drain current; typical values



$I_D = 400\text{ mA}$

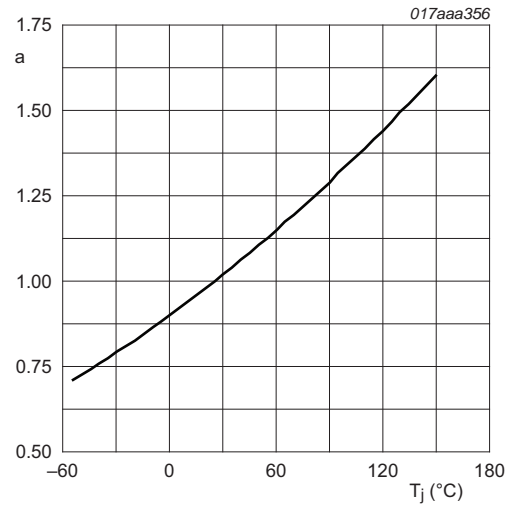
- (1) $T_j = 150\text{ }^\circ\text{C}$
- (2) $T_j = 25\text{ }^\circ\text{C}$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



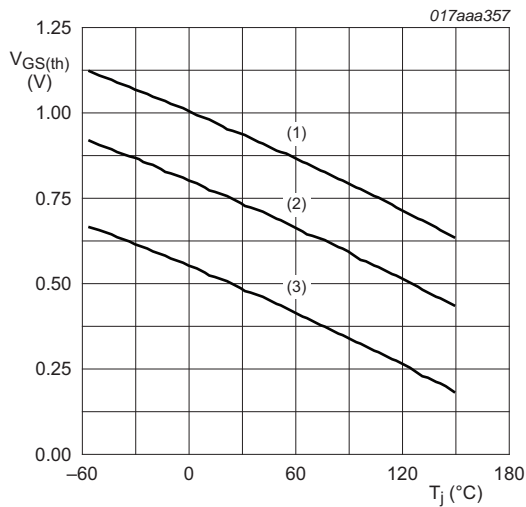
$V_{DS} > I_D \times R_{DS(on)}$
 (1) $T_j = 25\text{ °C}$
 (2) $T_j = 150\text{ °C}$

Fig 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values



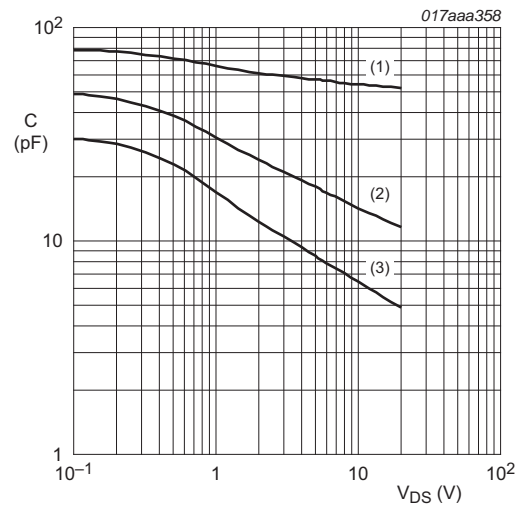
$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ C)}}$$

Fig 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values



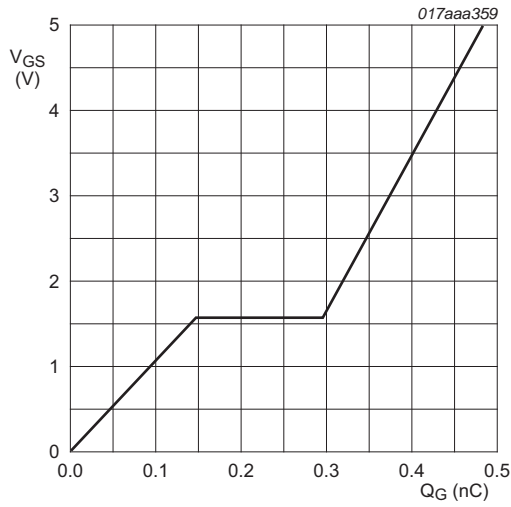
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$
 (1) maximum values
 (2) typical values
 (3) minimum values

Fig 13. Gate-source threshold voltage as a function of junction temperature



$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$
 (1) C_{iss}
 (2) C_{oss}
 (3) C_{rss}

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 0.5 \text{ A}; V_{DS} = 10 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 15. Gate-source voltage as a function of gate charge; typical values

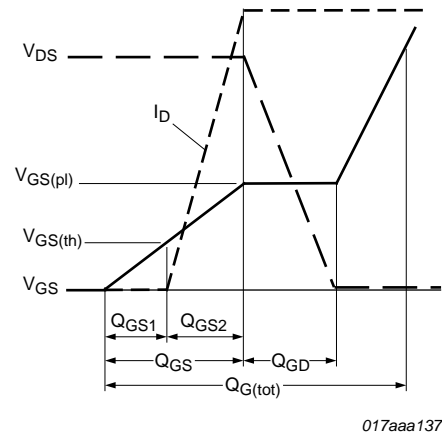
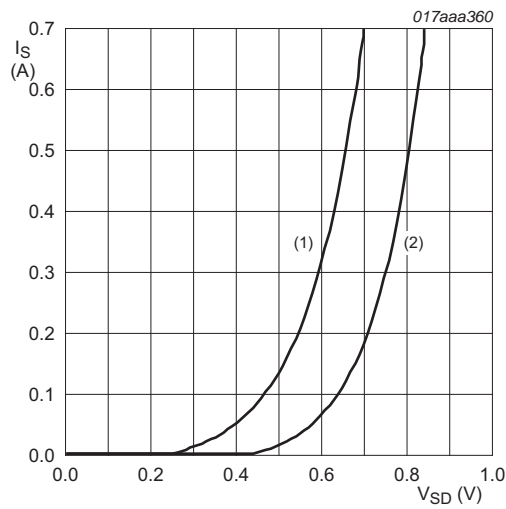


Fig 16. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$
 (1) $T_j = 150 \text{ }^\circ\text{C}$
 (2) $T_j = 25 \text{ }^\circ\text{C}$

Fig 17. Source current as a function of source-drain voltage; typical values

8. Test information



Fig 18. Duty cycle definition

9. Package outline

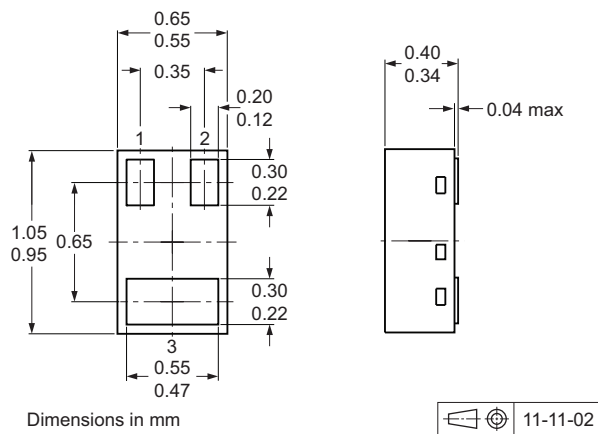
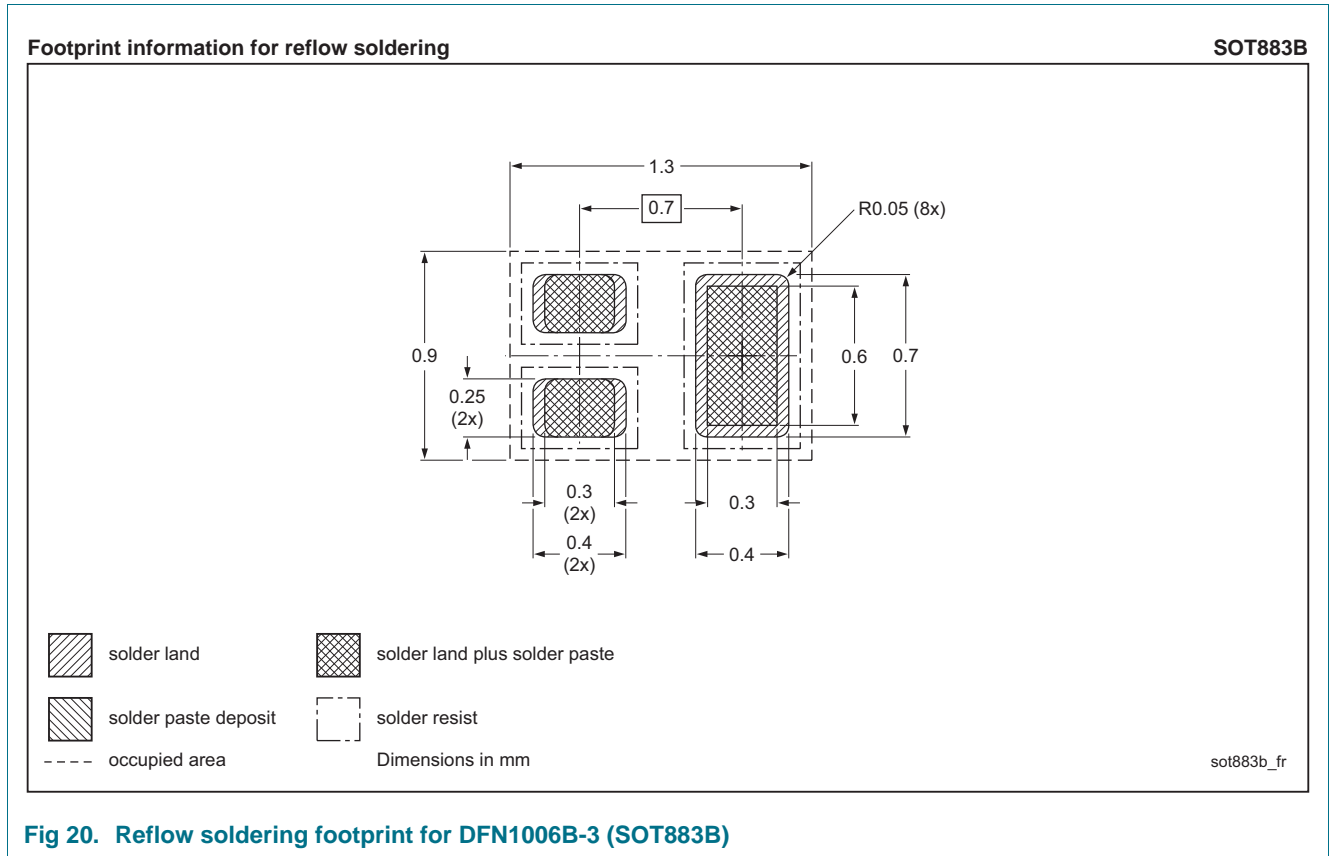


Fig 19. Package outline DFN1006B-3 (SOT883B)

10. Soldering



11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZB290UNE v.3	20120323	Product data sheet	-	PMZB290UNE v.2
Modifications:	• 1.2 "Features and benefits" corrected.			
PMZB290UNE v.2	20120207	Product data sheet	-	PMZB290UNE v.1
PMZB290UNE v.1	20120201	Product data sheet	-	-

12. Legal information

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Document status ^[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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Date of release: 23 March 2012

Document identifier: PMZB290UNE